DOSEM

Schmitt Buffer

NL17SG17

The NL17SG17 MiniGate[™] is an advanced high-speed CMOS Schmitt Buffer in ultra-small footprint.

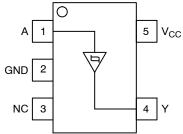
The NL17SG17 input structures provides protection when voltages up to 3.6 V are applied.

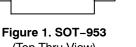
Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 3.7$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \,\mu A$ (Max) at $T_A = 25^{\circ}C$
- 3.6 V Overvoltage Tolerant (OVT) Input Pins
- IOFF Supports Partial Power Down Protection
- Ultra-Small Packages
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

NC

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GND 3 4 Figure 2. SC-88A

(Top View)

5 V_{CC}

Ο

(Top Thru View)

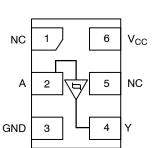


Figure 3. UDFN6 (Top View)

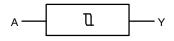
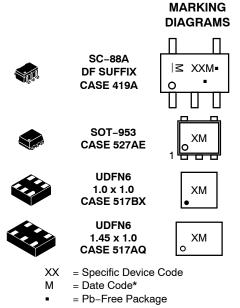


Figure 4. Logic Symbol



(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT							
SOT-953 SC-88A UDFN6							
1	А	NC	NC				
2	GND	А	A				
3	NC	GND	GND				
4	Y	Y	Y				
5	V _{CC}	V _{CC}	NC				
6			V _{CC}				

FUNCTION TABLE

A Input	Y Output
L	L
н	Н

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Table 1. MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +4.3	V
V _{IN}	DC Input Voltage		–0.5 to +4.3	V
V _{OUT}	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +4.3 -0.5 to +4.3	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-20	mA
I _{OUT}	DC Output Source/Sink Current		±20	mA
I _{CC or} I _{GND}	DC Supply Current Per Supply Pin or Ground F	Pin	±20	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case for 10 Sec	260	°C	
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 2)		154	°C/V
PD	Power Dissipation in Still Air		812	mW
θ_{JA}	Thermal Resistance (Note 2)	SC-88A SOT-953 UDFN6	377 254 154	°C/W
P _D	Power Dissipation in Still Air	SC-88A SOT-953 UDFN6	332 491 812	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{LATCHUP}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Applicable to devices with outputs that may be tri-stated.

2. Measured with minimum pad spacing on an FR4 board, using 10 mm - by - 1inch, 2 ounce copper trace no air flow per JESD51-7.

3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
4. Tested to EIA/JESD78 Class II.

Table 2. RECOMMENDED OPERATING CONDITIONS

Symbol	Para	Min	Max	Unit	
V _{CC}	Positive DC Supply Voltage		0.9	3.6	V
V _{IN}	Digital Input Voltage		0	3.6	V
V _{OUT}	Output Voltage	Active Mode (High or Low State) Tri-State Mode (Note 1) Power Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 3.6 3.6	V
T _A	Operating Free-Air Temperature		-55	+125	°C
t _r , t _f	Input Transition Rise or Fall Rate		0	No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Table 3. DC ELECTRICAL CHARACTERISTICS

			V _{CC} (V)	T _A = 25°C			T _A = −55°C to +125°C		
Symbol	Parameter	Conditions		Min	Тур	Max	Min	Max	Unit
V_{T+}	Positive Going		0.9	-	0.7	-	-	-	V
	Input Threshold Voltage		1.1	-	0.81	0.95	-	0.95	
	-		1.4	-	0.94	1.16	-	1.16	
			1.65	-	1.06	1.3	-	1.3	
			2.3	-	1.36	1.73	-	1.73	
			3.0	-	1.8	2.24	-	2.24	
V _{T-}	Negative Going		0.9	-	0.23	-	-	-	V
	Input Threshold Voltage		1.1	0.15	0.33	-	0.15	-	
	, , , , , , , , , , , , , , , , , , ,		1.4	0.3	0.47	_	0.3	-	
			1.65	0.35	0.6	_	0.35	-	
			2.3	0.55	0.85	_	0.55	-	
			3.0	0.95	1.13	_	0.95	-	
V _H	Hysteresis Voltage		0.9	-	0.27	_	-	-	V
			1.1	0.2	0.35	0.8	0.2	0.8	
			1.4	0.25	0.41	0.86	0.25	0.86	
			1.65	0.30	0.46	0.9	0.30	0.9	
			2.3	0.40	0.56	1.05	0.40	1.05	
		3.0	0.49	0.59	1.1	0.49	1.1		
V _{OH}	High-Level Output	V _{IN} = V _{IH} or V _{IL}							V
	Voltage	I _{OH} = –20 μA	0.9	-	0.75	_	-	_	
		I _{OH} = -0.3 mA		0.75 x V _{CC}	-	_	0.75 x V _{CC}	_	
		I _{OH} = -1.7 mA	1.4 to 1.6	0.75 x V _{CC}	-	_	0.75 x V _{CC}	_	
		I _{OH} = -3.0 mA	1.65 to 1.95	V _{CC} - 0.45	-	_	V _{CC} - 0.45	_	
		I _{OH} = -4.0 mA		2.0	_	_	2.0	_	
		I _{OH} = -8.0 mA	3.0 to 3.6	2.48	_	_	2.48	_	
V _{OL}	Low-Level Output								V
	Voltage	I _{OL} = 20 μA	0.9	-	0.1	-	-	-	1
		I _{OL} = 0.3 mA		-	_	0.25 x V _{CC}	-	0.25 x V _{CC}	
		I _{OL} = 1.7 mA		-	_	0.25 x V _{CC}	-	0.25 x V _{CC}	
		I _{OL} = 3.0 mA		-	-	0.45	-	0.45	
		I _{OL} = 4.0 mA		-	-	0.4	-	0.4	
		I _{OL} = 8.0 mA		-	_	0.4	-	0.4	
I _{IN}	Input Leakage Current	V _{IN} = 0 V to 3.6 V	0.9 to 3.6	-	-	±0.1	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 0 V to 3.6 V; V _{OUT} = 0 V to 3.6 V	0	-	-	1.0	-	10.0	μΑ
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	0.9 to 3.6	-	-	0.5	-	10.0	μΑ

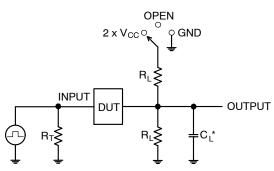
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

					T _A = 25 °C)	T _A −55°C to	_ = ⊳ +125°C		
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit	
t _{PLH} ,	Propagation Delay,	$C_L = 10 \text{ pF},$	0.9	-	47.2	-	-	-	ns	
PHL	^t рнL A to Y	A to Y $n_L = 1 \text{ IVIS2}$	$R_L = 1 M\Omega$	1.1 to 1.3	_	13.8	25.6	1.0	35.9	
			1.4 to 1.6	_	7.5	10.5	1.0	11.3		
			1.65 to 1.95	-	6.0	7.8	1.0	8.2		
		2.3 to 2.7	-	4.3	5.4	1.0	5.8			
			3.0 to 3.6	-	3.5	4.4	1.0	4.6		
		$C_L = 15 \text{ pF},$	0.9	-	48.6	-	-	-	ns	
		$R_L = 1 M\Omega$	1.1 to 1.3	-	14.3	26.3	1.0	41.8		
		C _L = 30 pF,	1.4 to 1.6	-	8.0	11.5	1.0	12.6		
			1.65 to 1.95	-	6.3	8.4	1.0	8.7		
			2.3 to 2.7	-	4.6	5.7	1.0	6.1		
			3.0 to 3.6	-	3.7	4.6	1.0	5.0		
			0.9	-	52.9	-	-	-	ns	
		$R_{L} = 1 M\Omega$	1.1 to 1.3	-	19.6	35.7	1.0	58.1		
			1.4 to 1.6	-	10.7	15.8	1.0	17.6		
			1.65 to 1.95	-	7.8	10.7	1.0	11.7		
			2.3 to 2.7	-	5.4	6.9	1.0	8.1		
			3.0 to 3.6	-	4.3	5.2	1.0	6.1		
C _{IN}	Input Capacitance		0 to 3.6		3	-	-	_	pF	
C _O	Output Capacitance	V _O = GND	0		3	-	-	-	pF	
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	_	-	pF	

Table 4. AC ELECTRICAL CHARACTERISTICS

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

performance may not be indicated by the Electrical Characteristics for the instead test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position
t _{PLH} / t _{PHL}	Open
t _{PLZ} / t _{PZL}	2 x V _{CC}
t _{PHZ} / t _{PZH}	GND

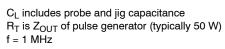
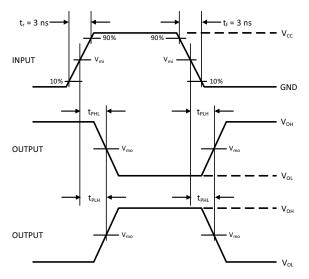


Figure 5. Test Circuit



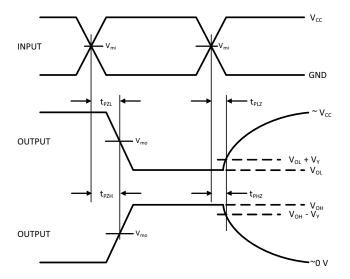


Figure 6. Switching Waveforms

V _{CC} , V	V _{mi} , V	V _{mo} , V	V _Y , V
0.9	V _{CC} /2	V _{CC} /2	0.1
1.1 to 1.3	V _{CC} /2	V _{CC} /2	0.1
1.4 to 1.6	V _{CC} /2	V _{CC} /2	0.1
1.65 to 1.95	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	1.5	1.5	0.3

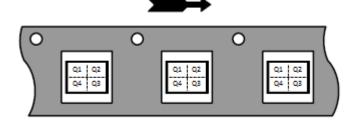
ORDERING INFORMATION

Device	Marking	Pin 1 Orientation (See below)	Package	Shipping [†]
NL17SG17DFT2G	AN	Q4	SC-88A	3000 / Tape & Reel
NL17SG17DFT2G-Q* (Contact onsemi)	AN	Q4	SC-88A	3000 / Tape & Reel
NL17SG17P5T5G	A (Rotated 90°CW)	Q2	SOT-953	8000 / Tape & Reel
NL17SG17MU1TCG (Contact onsemi)	5 (Rotated 180°CW)	Q4	UDFN6 1.45x1 mm	3000 / Tape & Reel
NL17SG17MU3TCG (Contact onsemi)	TBD	Q4	UDFN6 1x1 mm	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

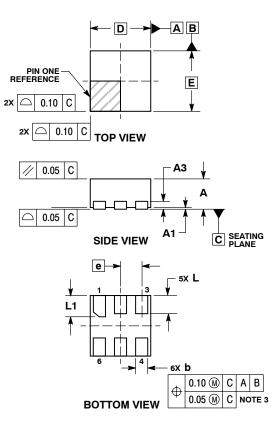
PIN 1 ORIENTATION IN TAPE AND REEL Direction of Feed



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PACKAGE DIMENSIONS

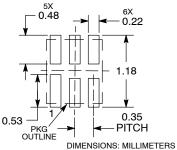
UDFN6, 1x1, 0.35P CASE 517BX ISSUE O



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
 4. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

BURRS AND MOLD FL						
	MILLIN	IETERS				
DIM	MIN	MAX				
Α	0.45	0.55				
A1	0.00 0.05					
A3	0.13 REF					
b	0.12	0.22				
D	1.00	BSC				
Е	1.00	BSC				
е	0.35 BSC					
L	0.25	0.35				
L1	0.30	0.40				

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

onsemi

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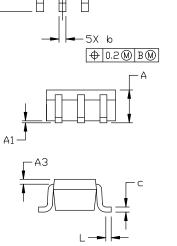
DATE 11 APR 2023



SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

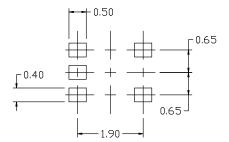
NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSDLETE. NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.



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RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS					
MIM	MIN.	NDM,	MAX.			
А	0.80	0.95	1.10			
A1			0.10			
AЗ		0.20 REF				
b	0.10	0.20	0.30			
С	0.10		0.25			
D	1.80	2.00	2.20			
E	2.00	2.10	2,20			
E1	1.15	1.25	1.35			
e		0.65 BS	С			
L	0.10	0.15	0.30			

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

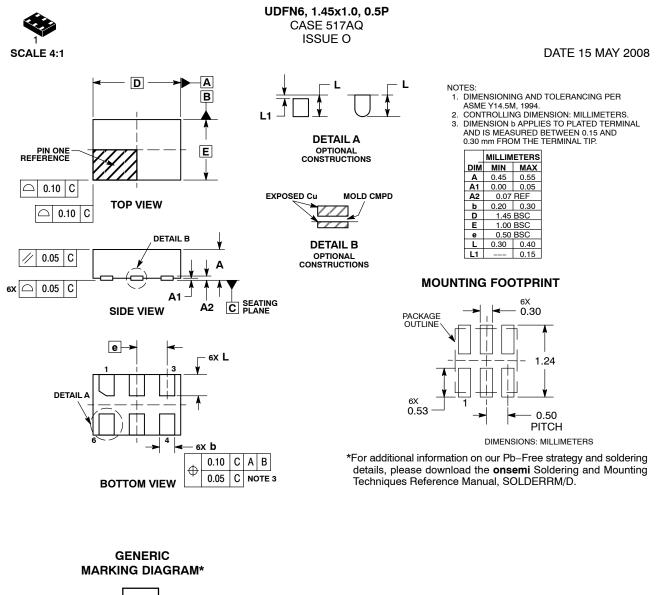
M = Date Code = Pb-Free Package

(Note: Microdot may be in either location)

DESCRIPTION:	SC-88A (SC-70-		ns are uncontrolled except w	vhen stamped "CONTROLLED (COPY" in red. PAGE 1 OF 1
DOCUMENT NUMBER:	98ASB42984B			t when accessed directly from	
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called efer to the device
STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	E

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XM

= Specific Device Code

Х

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " .", may or may not be present.

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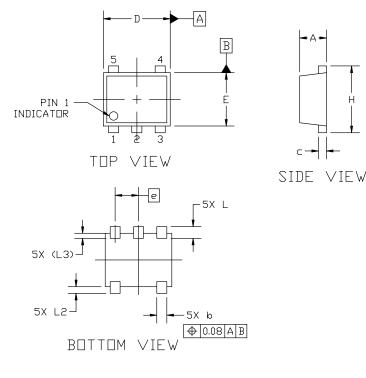


SOT-953 1.00x0.80x0.37, 0.35P CASE 527AE ISSUE F

DATE 17 JAN 2024

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



GENERIC MARKING DIAGRAM*



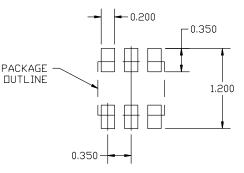
- X = Specific Device Code M = Month Code
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98AON26457D Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-953 1.00x0.80x0.37, 0.35P		PAGE 1 OF 1

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DIM	MIN	NDM	MAX		
A	0.34	0.37	0,40		
b	0.10	0,15	0.20		
С	0.07	0.12	0.17		
D	0.95	1.00	1.05		
E	0.75	0.80	0.85		
e	0.35 BSC				
Н	0.95	1.00	1.05		
L	0.125	0.175	0.225		
L2	0.05	0.10	0.15		
L3	0.075 (REF)				

MILL IMETERS



RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

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